

G0041



gp 2812

"Express Mail" mailing label number: EV214158857US

Date of Deposit: October 31, 2002

I hereby certify that this paper or fee is being deposited with the United States Postal Service "Express Mail Post Office to Addressee" service under 37 CFR 1.10 on the date indicated above and is addressed to: Box Non-Fee Amendment, Commissioner for Patents, Washington, D.C. 20231.

Typed or Printed Name of Person Mailing Paper or Fee: Linda Centrell

Signature: Linda Centrell



PATENT
Docket No.: P1316

IN THE
UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICANT: BIN YU

SERIAL NO.: 09/844,752

EXAMINER: POMPEY, R.E.

FILED: APRIL 27, 2001

ART UNIT: 2812

FOR: MOS TRANSISTOR WITH HIGHLY
LOCALIZED SUPER HALO IMPLANT

BOX NON-FEE AMENDMENT
COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

RECEIVED
TECHNOLOGY
NOV 5 2002
CENTER 2800

TRANSMITTAL LETTER

Dear Sir:

In connection with the above-referenced patent application, transmitted herewith are the following:

1. Amendment (6 pages) including Marked Up Version of the Claims (2 pages) total (8 pages);
2. Post card in acknowledgment of receipt of all transmitted materials.

Please date-stamp the enclosed post card and return same to the undersigned in acknowledgment of receipt of all transmitted material.

Respectfully submitted,


Victor Flores
Reg. No. 29,638

VF/rm

Date: 10/31/02
LARIVIERE, GRUBMAN & PAYNE, LLP
Post Office Box 3140
Monterey, CA 93942
(831) 649-8800

#713

11-13-02

Muller

"Express Mail" mailing label number: EV214158857US

Date of Deposit: October 31, 2002

I hereby certify that this paper or fee is being deposited with the United States Postal Service "Express Mail Post Office to Addressee" service under 37 CFR 1.10 on the date indicated above and is addressed to: Box Non-Fee Amendment, Commissioner for Patents, Washington, D.C. 20231.

Typed or Printed Name of Person Mailing Paper or Fee: Linda VentrellSignature: Linda VentrellPATENT
Docket No.: P1316IN THE
UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICANT: BIN YU

SERIAL NO.: 09/844,752 EXAMINER: POMPEY, R. E.

FILED: APRIL 27, 2001 ART UNIT: 2812

FOR: MOS TRANSISTOR WITH HIGHLY
LOCALIZED SUPER HALO IMPLANT

**BOX NON-FEE AMENDMENT
COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231**

RECEIVED
JULY CENTER 2800

AMENDMENT

Dear Sir:

In response to the Office Action dated August 14, 2002, Applicant respectfully requests entry of the following amendment.

In the Claims:

Please amend claims 1, 5, and 10 as follows:

- BT
~~new claim~~
1. (AMENDED) A method of making a MOSFET, comprising:
providing a substrate having a gate oxide and gate thereon, the gate defining a channel region of no more than 50 nm length;
performing a source/drain extension implant;
forming a spacer on the gate;